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(71)Applicant : NIPPON MINING CO LTD

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(72)Inventor : SUGA KAZUHIKO
KAISHIYOU TAKASHI
IZUMI SEIICHI

(54) EPITAXIAL GROWTH METHOD

(57)Abstract:

PURPOSE: To drastically lower an abnormally grown defect by performing specified specular finishing on the surface of a wafer and specifying the temp. of a base plate in the case of growing an epitaxial layer on the surface of the wafer by an organic metallic vapor phase epitaxial growth method.

CONSTITUTION: Epitaxial growth is performed by utilizing a wafer wherein the face orientation is tilted at 0.1–0.5° preferably 0.1–0.2° from (100) direction and raising the temp. of a base plate at 600–700° C. By this method, an epitaxial layer is grown uniformly and densely in the whole surface and a defect accompanied with growth is made difficult to be caused. Further the range of a product heretofore called as a face orientation just article is limited at ≤0.1° off angle. This is discriminated from the wafer having 0.1–0.5° off angle and therefore it can be prevented that the defect is caused or not on the surface of the epitaxial layer.

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